LITE-ON SEMICONDUCTOR

T4M10T-B SERIES

Sensitive Gate Triacs
Sillicon Bidirectional Thyristors

TRIACS
4 AMPERES RMS
600 VOLTS

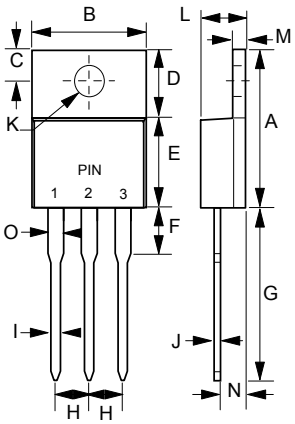
FEATURES

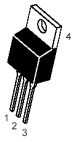
- Sensitive Gate Allows Triggering by Microcontrollers and other Logic Circuits
- High Immunity to dv/dt - 50 V/us Minimum at 125℃
- Commutating di/dt - 3.0 A/ms Minimum at 125℃
- Minimum and Maximum Values of IGT, VGT and IH Specified for Ease of Design
- On-State Current Rating of 4 Amperes RMS at 100℃
- High Surge Current Capability - 40 Amperes
- Blocking Voltage to 800 Volts
- Rugged, Economical TO220AB Package
- Operational in Three Quadrants: Q1, Q2, and Q3
- Pb-Free Package

MECHANICAL DATA

- Case: Molded plastic
- Weight: 0.07 ounces, 2.0 grams

TO-220AB





TO-220AB		
DIM.	MIN.	MAX.
A	14.22	15.88
B	9.65	10.67
C	2.54	3.43
D	5.84	6.86
E	8.26	9.28
F	-	6.35
G	12.70	14.73
H	2.29	2.79
I	0.51	1.14
J	0.40	0.67
K	3.53⌀	4.09⌀
L	3.56	4.83
M	1.14	1.40
N	2.03	2.92
O	1.17	1.37
All Dimensions in millimeter		

PIN ASSIGNMENT	
1	Main Terminal 1
2	Main Terminal 2
3	Gate
4	Main Terminal 2

MAXIMUM RATINGS (Tj= 25℃ unless otherwise noticed)

Rating	Symbol	Value	Unit
Peak Repetitive Off– State Voltage (1) (TJ= -40 to 125℃, Sine Wave, 50 to 60 Hz; Gate Open) T4M10T600B	VDRM, VRRM	600	Volts
On-State RMS Current (Full Cycle Sine Wave 50 to 60 Hz, TC =100℃)	IT(RMS)	4.0	Amp
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, TJ= 25℃)	ITSM	40	Amps
Circuit Fusing Consideration (t = 8.3 ms)	I^2t	6.6	A^2s
Peak Gate Power (TC = 100℃, Tp≦ 1.0 us)	PGM	0.5	Watt
Average Gate Power (TC = 100℃, t=8.3 ms)	PG(AV)	0.1	Watt
Operating Junction Temperature Range	TJ	-40 to +125	℃
Storage Temperature Range	Tstg	-40 to +150	℃

Notice: (1) VDRM and VRRM for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

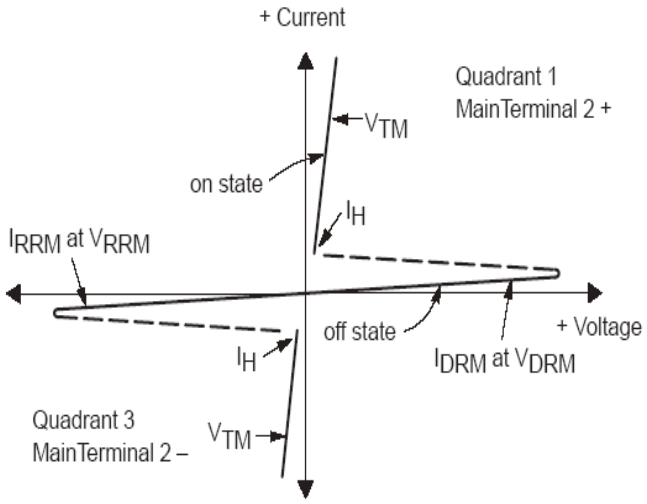
THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance - Junction to Case - Junction to Ambient	RthJC RthJA	2.2 62.5	℃/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	T_L	260	℃

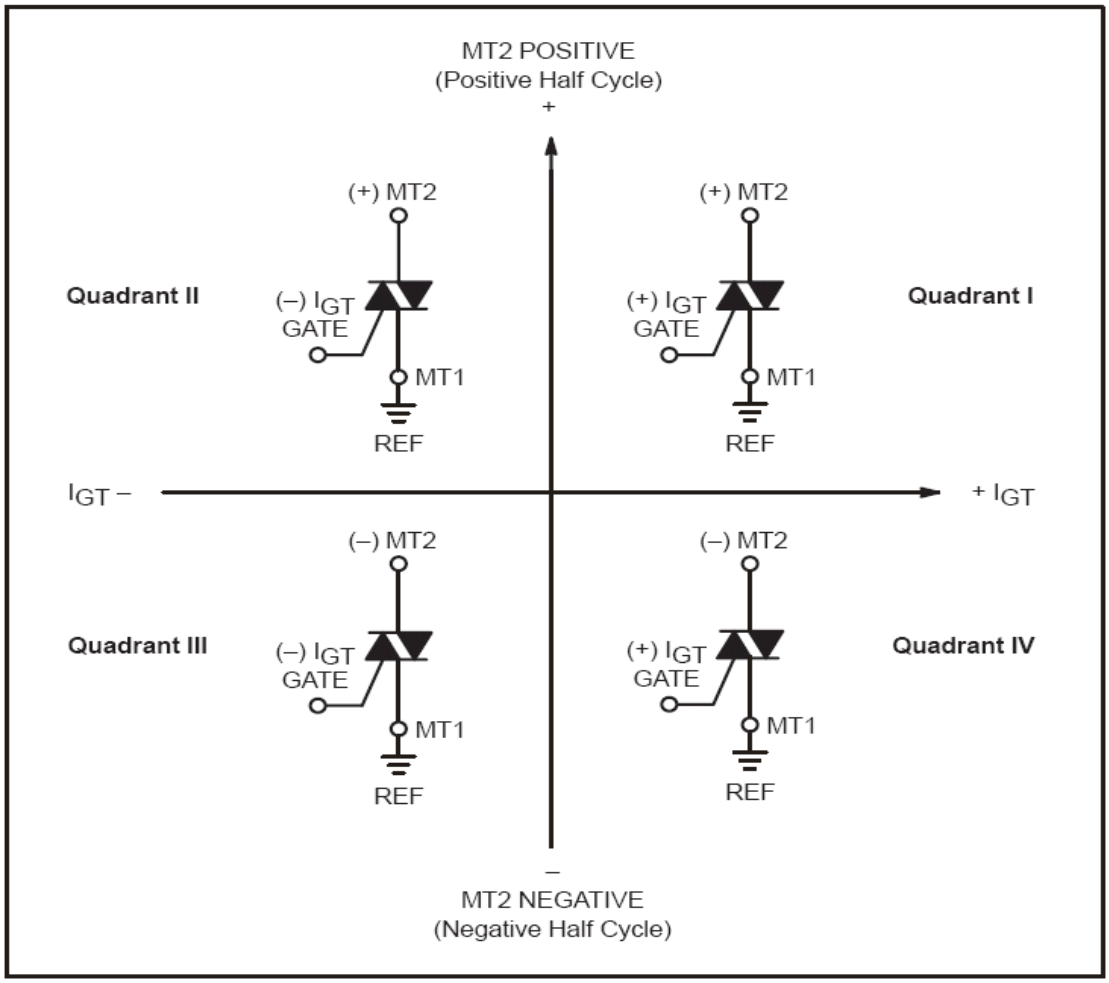
ELECTRICAL CHARACTERISTICS (T_J=25℃ unless otherwise noted; Electrical apply in both directions)

Characteristics	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Peak Reptitive Forward or Reverse Blocking Current T_J=25℃ (V_D=Rated V_{DRM}, V_{RRM}; Gate Open) T_J=125℃	I_{DRM} I_{RRM}	---- ----	---- ----	10 2.0	uA mA
ON CHARACTERISTICS					
Peak On-State Voltage (I_{TM}=± 6A Peak @Tp ≦2.0 ms, Duty Cycle ≦ 2%)	V_{TM}	----	1.3	1.6	Volts
Gate Trigger Current (V_D = 12V; R_L = 100 Ohms)	I_{GT1} I_{GT2} I_{GT3}	2.9 2.9 2.9	4.0 4.7 6.0	10 10 10	mA
Gate Trigger Voltage (V_D = 12 V; R_L =100 Ohms)	V_{GT1} V_{GT2} V_{GT3}	0.5 0.5 0.5	0.70 0.65 0.70	1.3 1.3 1.3	Volts
Latching Current (V_D = 12 V, IG = 10 mA)	I_{L1} I_{L2} I_{L3}	---- ---- ----	6.0 15 6.0	30 30 30	mA
Holding Current (V_D = 12 V, Initiating Current = ± 200 mA, Gate Open)	I_H	2.0	5.0	15	mA
DYNAMIC CHARACTERISTICS					
Critical Rate of Rise of Off-State Voltage (V_D=0.67 x Rated V_{DRM}, Exponential Waveform, Gate Open, T_J=125℃)	dv/dt	50	150	----	V/us
Repetitive Critical Rate of Rise of On-State Current IPK = 50 A; PW = 40 usec; diG/dt = 200 mA/usec; f = 60 Hz	di/dt	----	----	10	A/us
Rate of Change of Commutating Current (V_D = 400 V, I_{TM} = 3.5A, Commutating dv/dt = 10 V/us, Gate Open, T_J = 125℃, f = 500 Hz, C_L = 5.0 uF, L_L = 20 mH, No Snubber)	(di/dt)c	3.0	4.0	----	A/ms

Symbol	Parameter
V_{DRM}	Peak Repetitive Forward Off State Voltage
I_{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Reverse Off State Voltage
I_{RRM}	Peak Reverse Blocking Current
V_{TM}	Maximum On State Voltage
I_H	Holding Current



Quadrant Definitions



All polarities are referenced to MT1
Whith in -phase signal (using standard AC lines) quadrants I and III are used

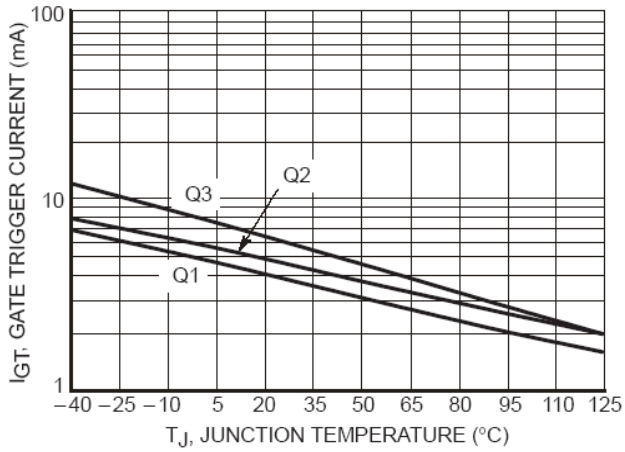


Figure 1. Typical Gate Trigger Current versus Junction Temperature

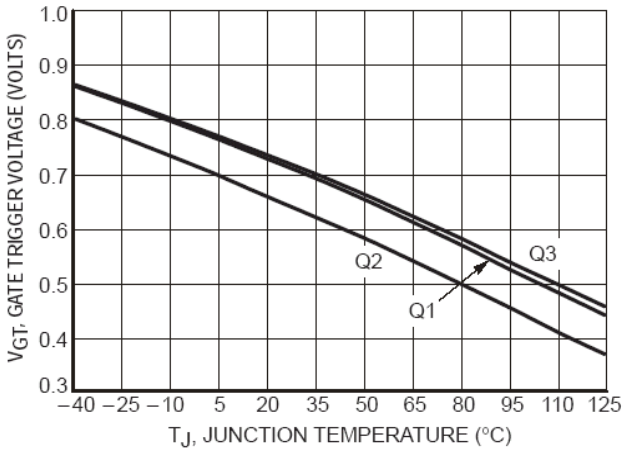


Figure 2. Typical Gate Trigger Voltage versus Junction Temperature

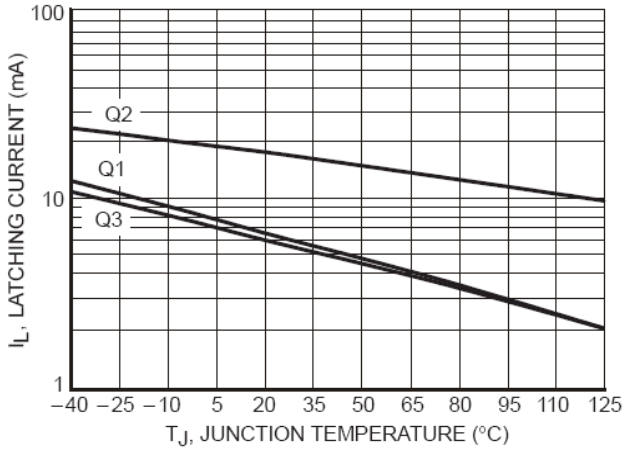


Figure 3. Typical Latching Current versus Junction Temperature

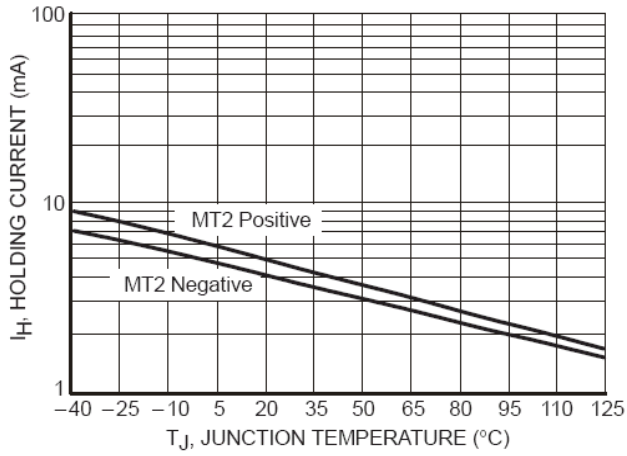


Figure 4. Typical Holding Current versus Junction Temperature

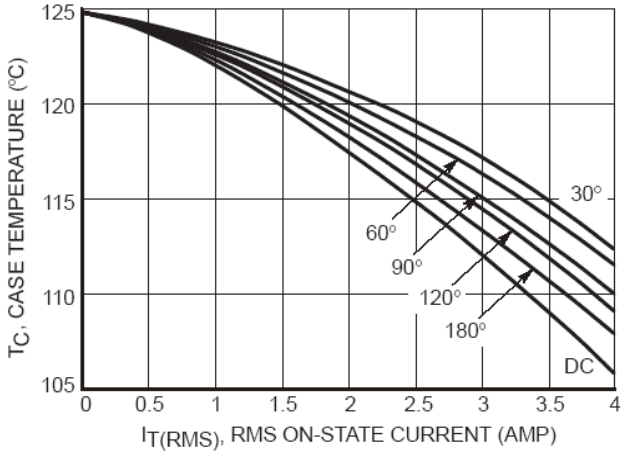


Figure 5. Typical RMS Current Derating

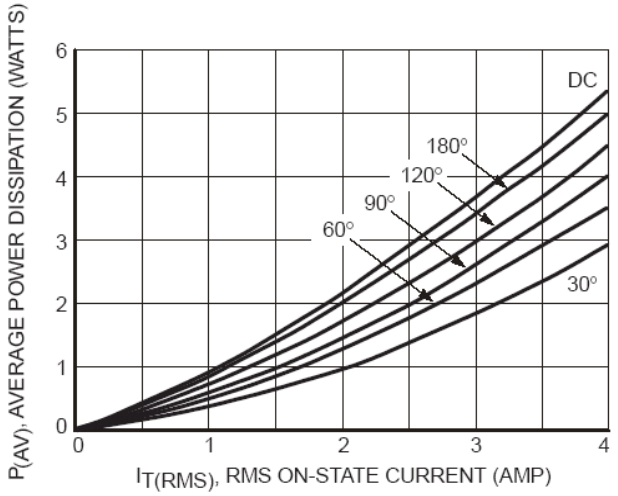


Figure 6. On-State Power Dissipation

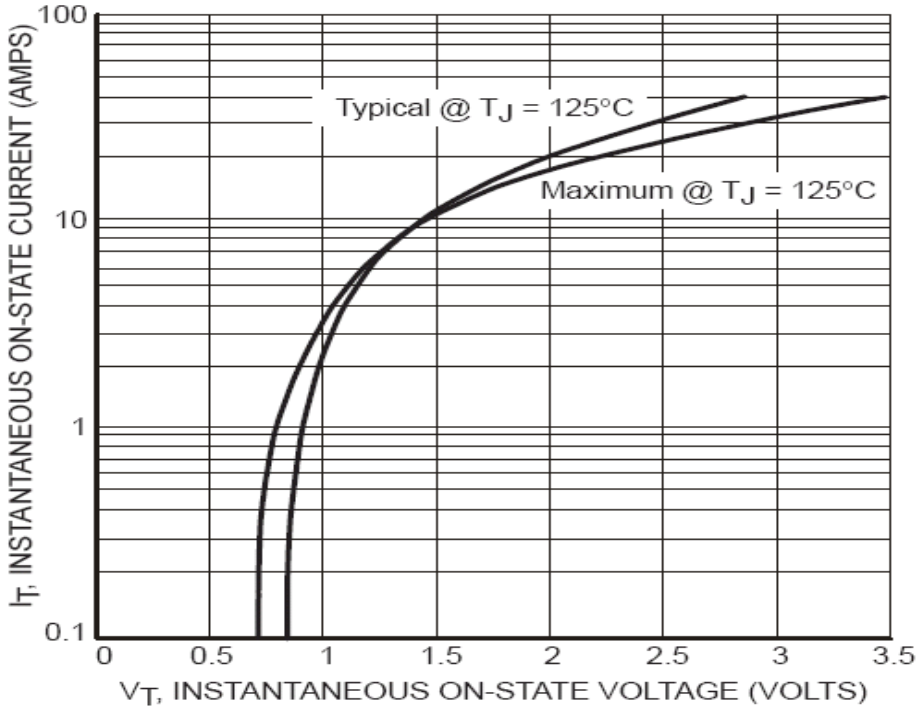


Figure 7. Typical On-State Characteristics

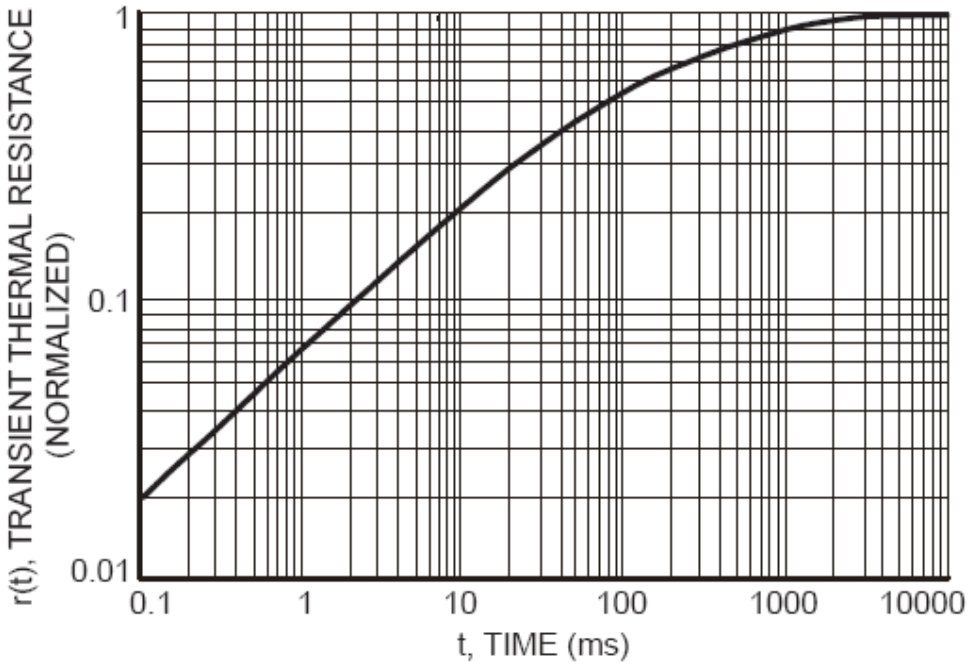


Figure 8. Typical Thermal Response

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